# ON Semiconductor®

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# P-Channel Power MOSFET -12V, -6.0A, 35mΩ, Single MCPH6

#### **Features**

- On-resistance  $R_{DS}(on)1=29m\Omega(typ.)$
- Halogen free compliance

- 1.5V drive
- Protection diode in

#### **Specifications**

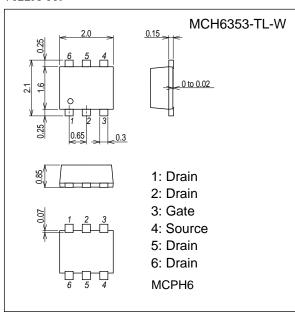
**Absolute Maximum Ratings** at Ta = 25°C

| Parameter                   | Symbol           | Conditions   | Ratings      | Unit |
|-----------------------------|------------------|--|--------------|------|
| Drain to Source Voltage     | V <sub>DSS</sub> |  | -12          | V    |
| Gate to Source Voltage      | VGSS             |  | ±10          | V    |
| Drain Current (DC)          | ID               |  | -6.0         | Α    |
| Drain Current (Pulse)       | I <sub>DP</sub>  | PW≤10μs, duty cycle≤1%   | -24          | Α    |
| Allowable Power Dissipation | PD               | When mounted on ceramic substrate (1500mm <sup>2</sup> ×0.8mm) | 1.4          | W    |
| Channel Temperature         | Tch              |  | 150          | °C   |
| Storage Temperature         | Tstg             |  | - 55 to +150 | °C   |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Package Dimensions**

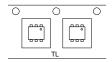
unit : mm (typ) 7022A-009



#### Ordering & Package Information

| Device       | Package                            | Shipping             | note                           |  |
|--------------|------------------------------------|----------------------|--------------------------------|--|
| MCH6353-TL-W | MCPH6<br>SC-88,SC-70-6,<br>SOT-363 | 3,000<br>pcs. / reel | Pb-Free<br>and<br>Halogen Free |  |

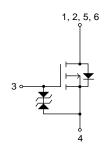
#### Packing Type: TL



#### Marking



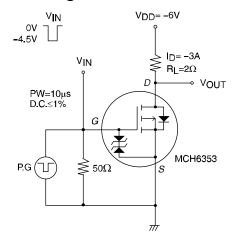
#### **Electrical Connection**

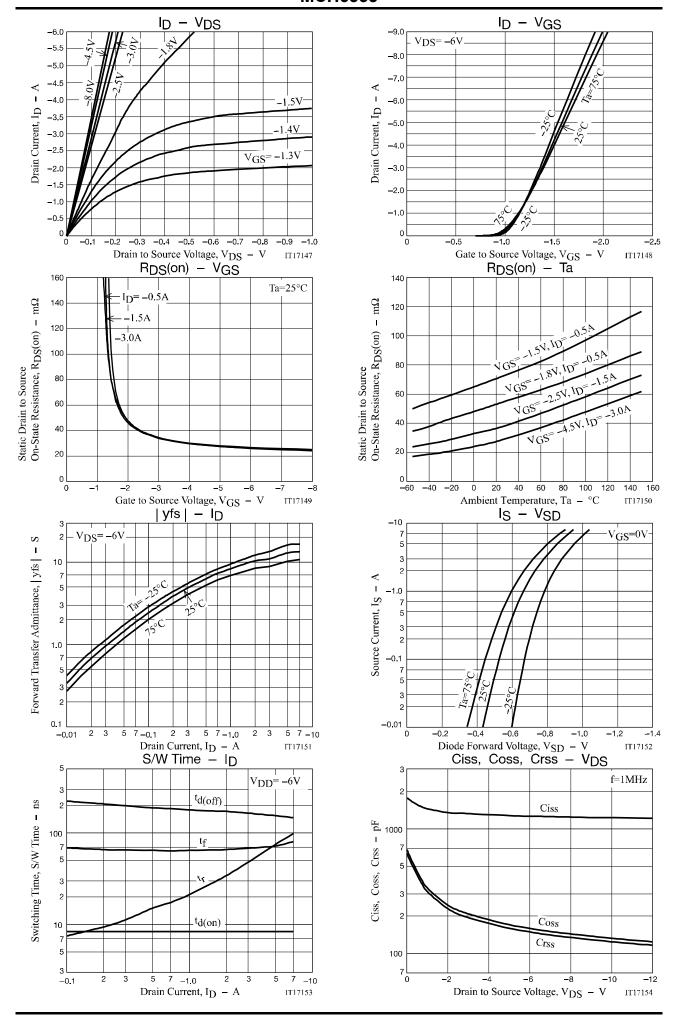


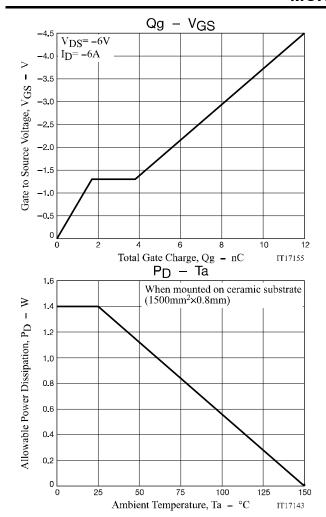
#### **Electrical Characteristics** at Ta = 25°C

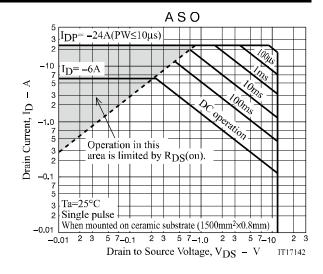
| Parameter                                     | Symbol                | Conditions  | Ratings |      |      | 1.1  |
|---|-----------------------|---|---------|------|------|------|
| Parameter                                     |                       |   | min     | typ  | max  | Unit |
| Drain to Source Breakdown Voltage             | V(BR)DSS              | I <sub>D</sub> =-1mA, V <sub>G</sub> S=0V                         | -12     |      |      | >    |
| Zero-Gate Voltage Drain Current               | IDSS                  | V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V                        |         |      | -1   | μΑ   |
| Gate to Source Leakage Current                | IGSS                  | V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V                         |         |      | ±1   | μΑ   |
| Cutoff Voltage                                | V <sub>GS</sub> (off) | V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA                        | -0.4    |      | -1.4 | >    |
| Forward Transfer Admittance                   | yfs                   | V <sub>DS</sub> =-6V, I <sub>D</sub> =-3A                         |         | 11   |      | S    |
|   | R <sub>DS</sub> (on)1 | I <sub>D</sub> =-3A, V <sub>G</sub> S=-4.5V                       |         | 29   | 35   | mΩ   |
| Static Drain to Source On-State<br>Resistance | R <sub>DS</sub> (on)2 | I <sub>D</sub> =-1.5A, V <sub>G</sub> S=-2.5V                     |         | 38   | 48   | mΩ   |
|   | R <sub>DS</sub> (on)3 | I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-1.8V                     |         | 52   | 78   | mΩ   |
|   | R <sub>DS</sub> (on)4 | I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-1.5V                     |         | 70   | 140  | mΩ   |
| Input Capacitance                             | Ciss                  |   |         | 1250 |      | pF   |
| Output Capacitance                            | Coss                  | V <sub>DS</sub> =-6V, f=1MHz                                      |         | 160  |      | pF   |
| Reverse Transfer Capacitance                  | Crss                  |   |         | 150  |      | pF   |
| Turn-ON Delay Time                            | t <sub>d</sub> (on)   |   |         | 8.4  |      | ns   |
| Rise Time                                     | t <sub>r</sub>        | Construction of Track Circuit                                     |         | 48   |      | ns   |
| Turn-OFF Delay Time                           | t <sub>d</sub> (off)  | See specified Test Circuit.                                       |         | 165  |      | ns   |
| Fall Time                                     | tf                    |   |         | 68   |      | ns   |
| Total Gate Charge                             | Qg                    |   |         | 12   |      | nC   |
| Gate to Source Charge                         | Qgs                   | V <sub>DS</sub> =-6V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A |         | 1.7  |      | nC   |
| Gate to Drain "Miller" Charge                 | Qgd                   | ]   |         | 2.1  |      | nC   |
| Diode Forward Voltage                         | V <sub>SD</sub>       | I <sub>S</sub> =-6A, V <sub>GS</sub> =0V                          |         | -0.9 | -1.2 | V    |

## **Switching Time Test Circuit**



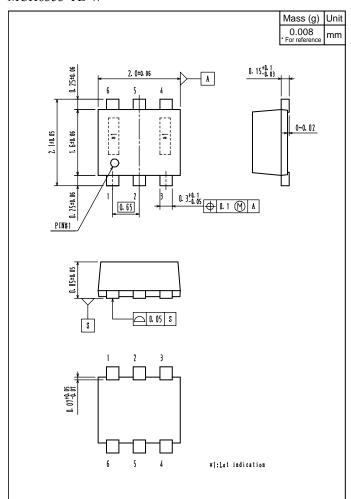




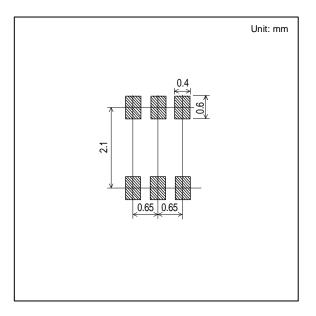


#### **Outline Drawing**

MCH6353-TL-W



### **Land Pattern Example**



Note on usage: Since the MCH6353 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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